

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph 40 with the following amended paragraph:

[0040] FIG. 11 is a cross-sectional view of the capacitor 10 illustrated in FIG. 10 in an early stage of fabrication wherein a layer of HSG polysilicon 60 is formed in the opening 28 and on the top surface of the substrate assembly 18. The layer of HSG polysilicon 60 may be formed, for example, with a CVD process. The interconnect 20 is recessed below the bottom surface of the opening ~~[[26]]~~ 28.